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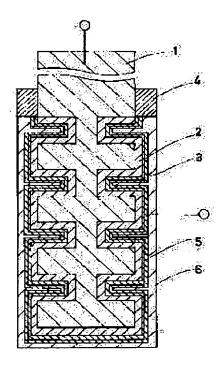
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## (54) MANUFACTURE OF CAPACITOR

## (57)Abstract:

PROBLEM TO BE SOLVED: To provide the manufacturing method of a small type capacitor having a large capacitance, a small leakage current, high withstand voltage and high reliability.

SOLUTION: After a high molecular dielectric thin film 2 has been formed in a vapor phase atmosphere on the surfaceroughened electrode 1, opposing electrodes 3, 5 and 6 are formed on the surface of the high molecular dielectric thin film 2. As the high molecular dielectric thin film 2 is formed in vapor phase on the surface of the surface-roughened electrode 1 as above-mentioned, it is favorable to form the objective high purity composition on the surface of the electrode 1, and also it is effective to prevent the oxidation of the electrode 1. As a result, a highly reliable small type and large capaitance capacitor, having a small leakage current, high withsand voltage and no polarity, can be manufactured. Also, by the formation of the high molecular thin film 2 after formation of the high molecular dielectric thin film 2 by a sputtering method, its characteristics can be improved.



## **LEGAL STATUS**

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